

ABSTRACT

A method for fabricating a semiconductor light-emitting element according to the present invention includes the steps of (A) providing a striped masking layer on a first Group III-V compound semiconductor, (B) selectively growing a second Group III-V compound semiconductor over the entire surface of the first Group III-V compound semiconductor except a portion covered with the masking layer, thereby forming a current confining layer that has a striped opening defined by the masking layer, (C) selectively removing the masking layer, and (D) growing a third Group III-V compound semiconductor to cover the surface of the first Group III-V compound semiconductor, which is exposed through the striped opening, and the surface of the current confining layer.